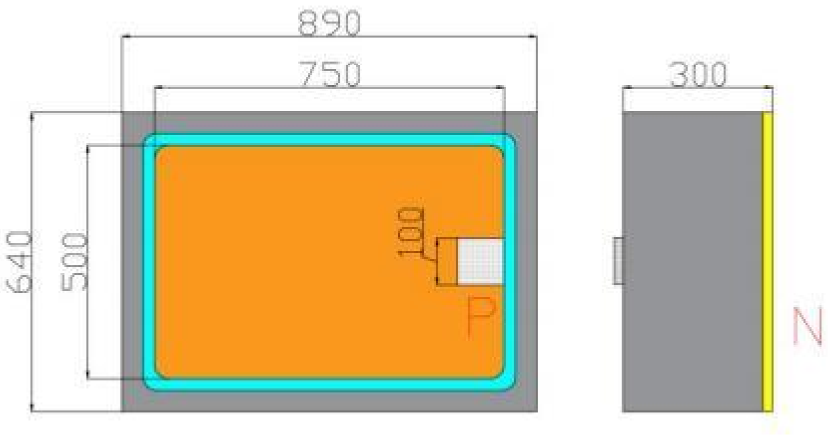
890x640um Silicon PD Chip datasheet

P/N : WS94-01C



Feature

Si PIN photodiode chip

Structure

Planar type : PN diode
Electrodes :
Back side (Cathode) : Gold
Top side (Anode) : Aluminum

DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	750 × 500			µm
Chip width	640			µm
Chip length	890			µm
Chip height	280	300	320	µm
Pad Area		100		µm

Electro-Optical Characteristics (@ Ta=25 ℃)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=10mA, H=0	0.5		1.3	V
Reverse Voltage	Vbr	Ir=100µA, H=0	60			V
Reverse Dark Current	Id	Vr=10V, H=0			10	nA
Capacitance	Cj	VR=3V, H=0, F=1MHz		10		pF
Sensitive Wavelength Range	λ		430		1000	nm
Reverse light Current	IL	VR =5V, 1 mW/cm2 @940nm		2		uA